

DATA SHEET

BTH151S-650R

Thyristor

High Repetitive Surge

Product specification

March 2001



WeEn

WeEn Semiconductors

Thyristor High Repetitive Surge

BTH151S-650R

GENERAL DESCRIPTION

Passivated thyristor in a plastic envelope, suitable for surface mounting, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. This thyristor has a high repetitive surge specification which makes it suitable for applications where high inrush currents or stall currents are likely to occur on a repetitive basis.

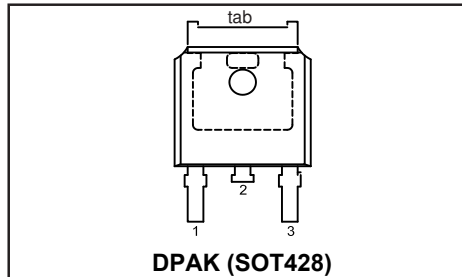
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	650	V
$I_{T(AV)}$	Average on-state current	7.5	A
$I_{T(RMS)}$	RMS on-state current	12	A
I_{TSM}	Non-repetitive peak on-state current	110	A
I_{TRM}	Repetitive peak on-state current	60	A

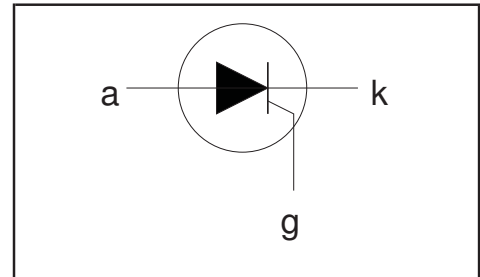
PINNING - SOT428

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	half sine wave;	-	650	V
$I_{T(AV)}$	Average on-state current	$T_{mb} \leq 103\text{ }^{\circ}\text{C}$	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	12	A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge	-	110	A
		$t = 10\text{ ms}$	-	121	A
I_{TRM}	Repetitive peak on-state current	$t = 10\text{ms}, \tau = 3\text{s}, T_{mb} \leq 45\text{ }^{\circ}\text{C}, \text{no. of surges} = 100\text{k}$	-	60	A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	61	A^2s
di_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20\text{ A}; I_G = 50\text{ mA}; di_G/dt = 50\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current		-	2	A
V_{GM}	Peak gate voltage		-	5	V
V_{RGM}	Peak reverse gate voltage		-	5	V
P_{GM}	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5	W
T_{stg}	Storage temperature		-40	150	$^{\circ}\text{C}$
T_j	Operating junction temperature		-	125	$^{\circ}\text{C}$

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base		-	-	1.8	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	pcb (FR4) mounted; footprint as in Fig.14	-	75	-	K/W

STATIC CHARACTERISTICS

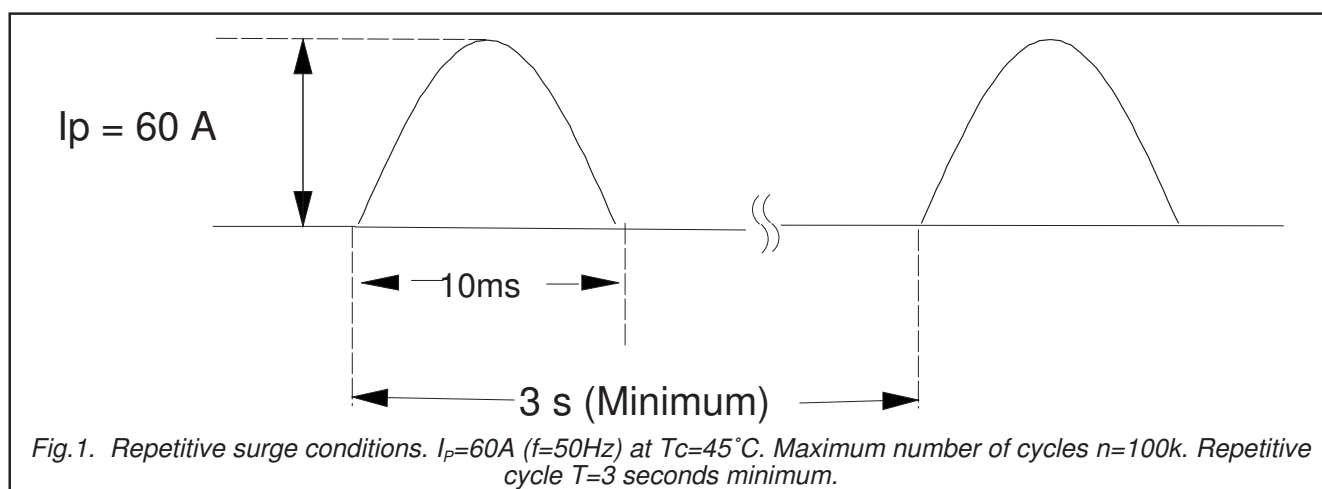
$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	2	15	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	10	40	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	7	20	mA
V_T	On-state voltage	$I_T = 23\text{ A}$	-	1.4	1.75	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.6	1.5	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C}$	0.25	0.4	-	V
		$V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

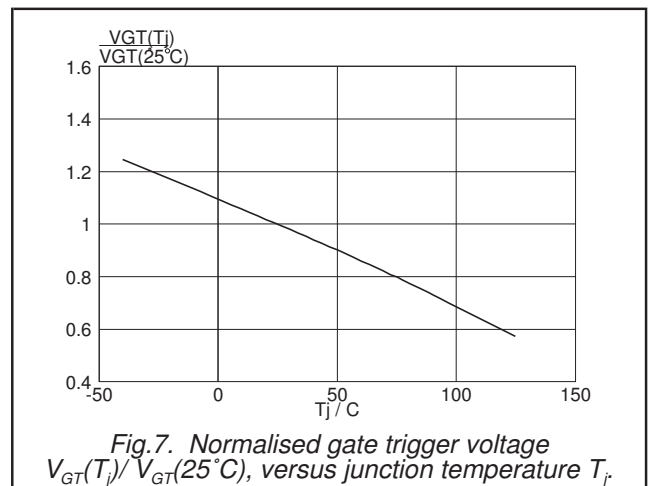
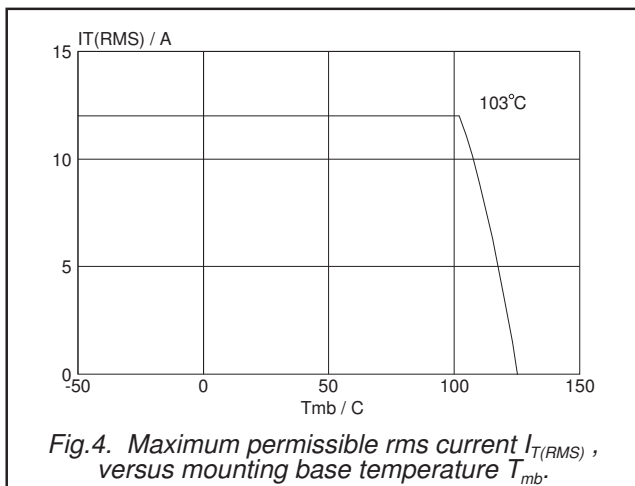
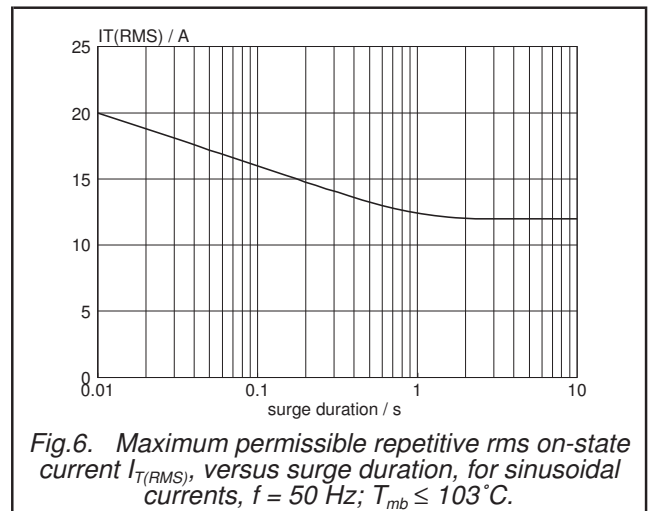
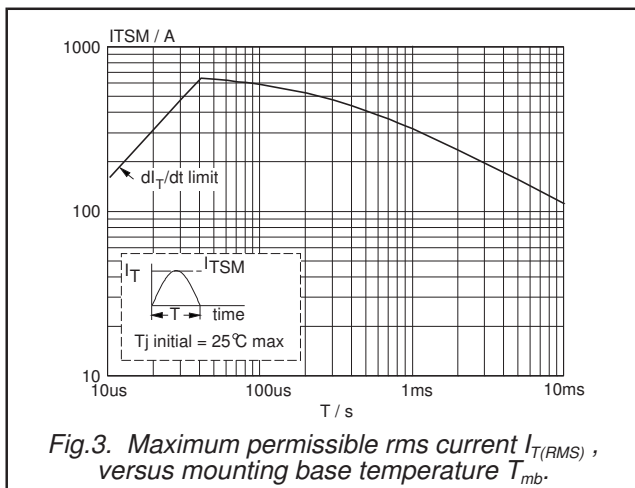
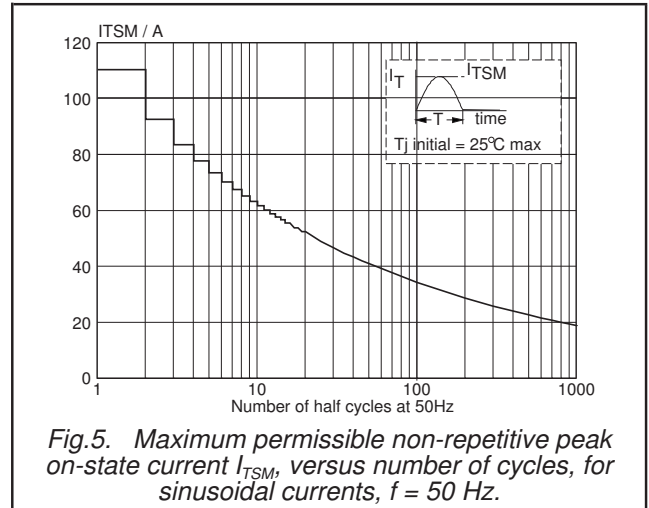
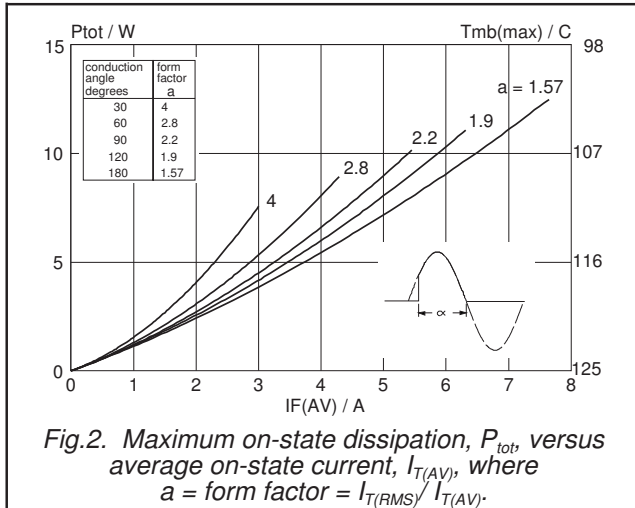
$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ exponential waveform;				
		Gate open circuit $R_{GK} = 100\ \Omega$	50 200	130 1000	-	V/ μs V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 40\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs
t_q	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ $I_{TM} = 20\text{ A}; V_R = 25\text{ V}; dI_{TM}/dt = 30\text{ A}/\mu\text{s};$ $dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK} = 100\ \Omega$	-	70	-	μs



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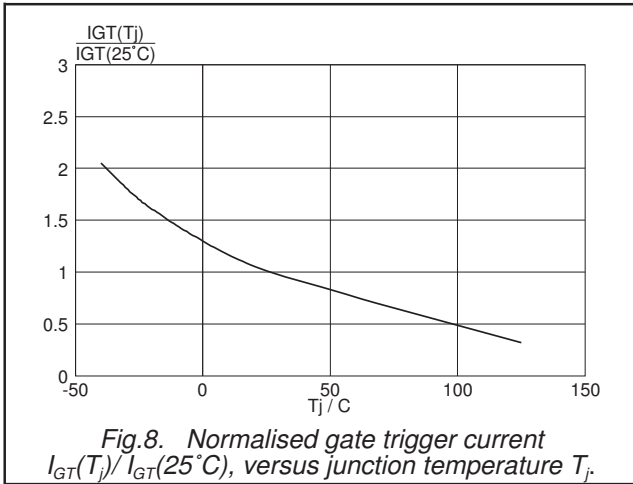


Fig.8. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

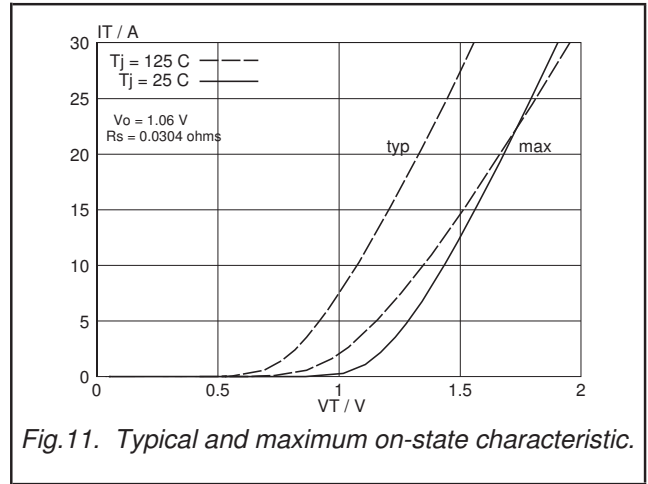


Fig.11. Typical and maximum on-state characteristic.

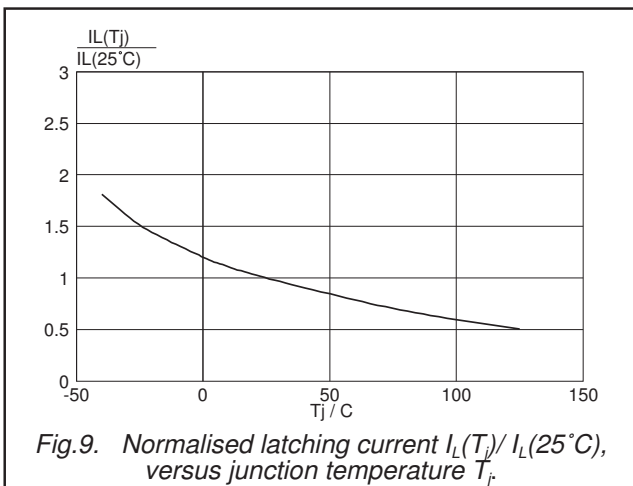


Fig.9. Normalised latching current $I_L(T_j)/I_L(25^\circ\text{C})$, versus junction temperature T_j .

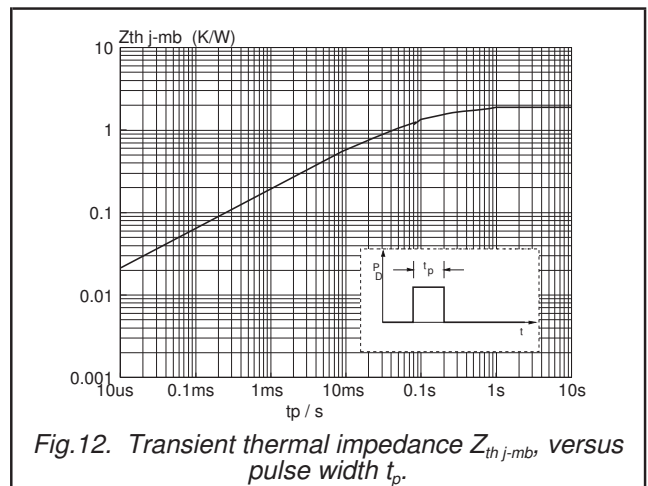


Fig.12. Transient thermal impedance $Z_{th\ j-mb}$, versus pulse width t_p .

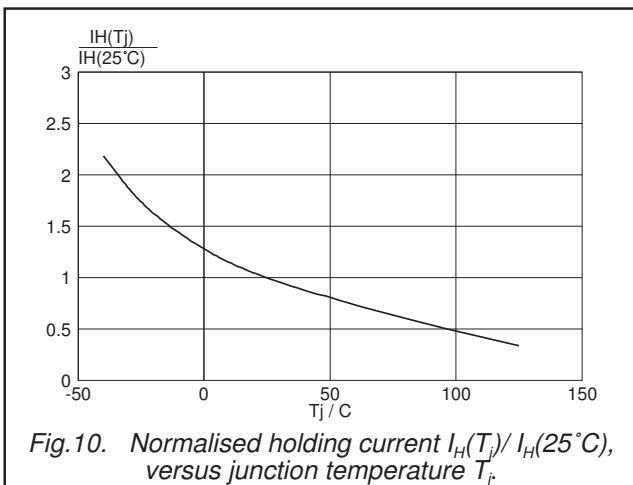


Fig.10. Normalised holding current $I_H(T_j)/I_H(25^\circ\text{C})$, versus junction temperature T_j .

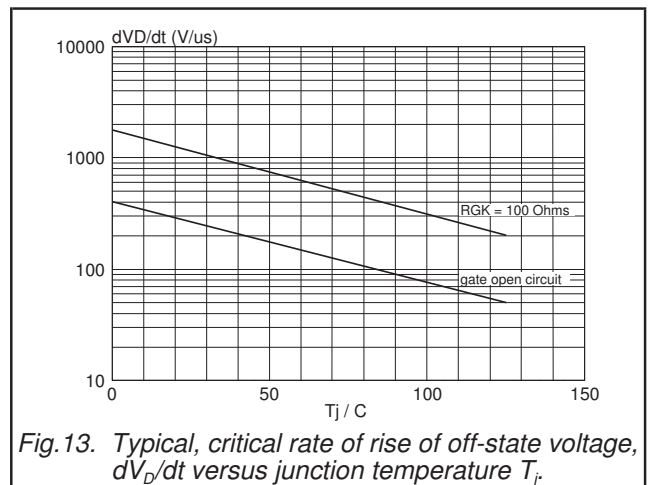


Fig.13. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j .

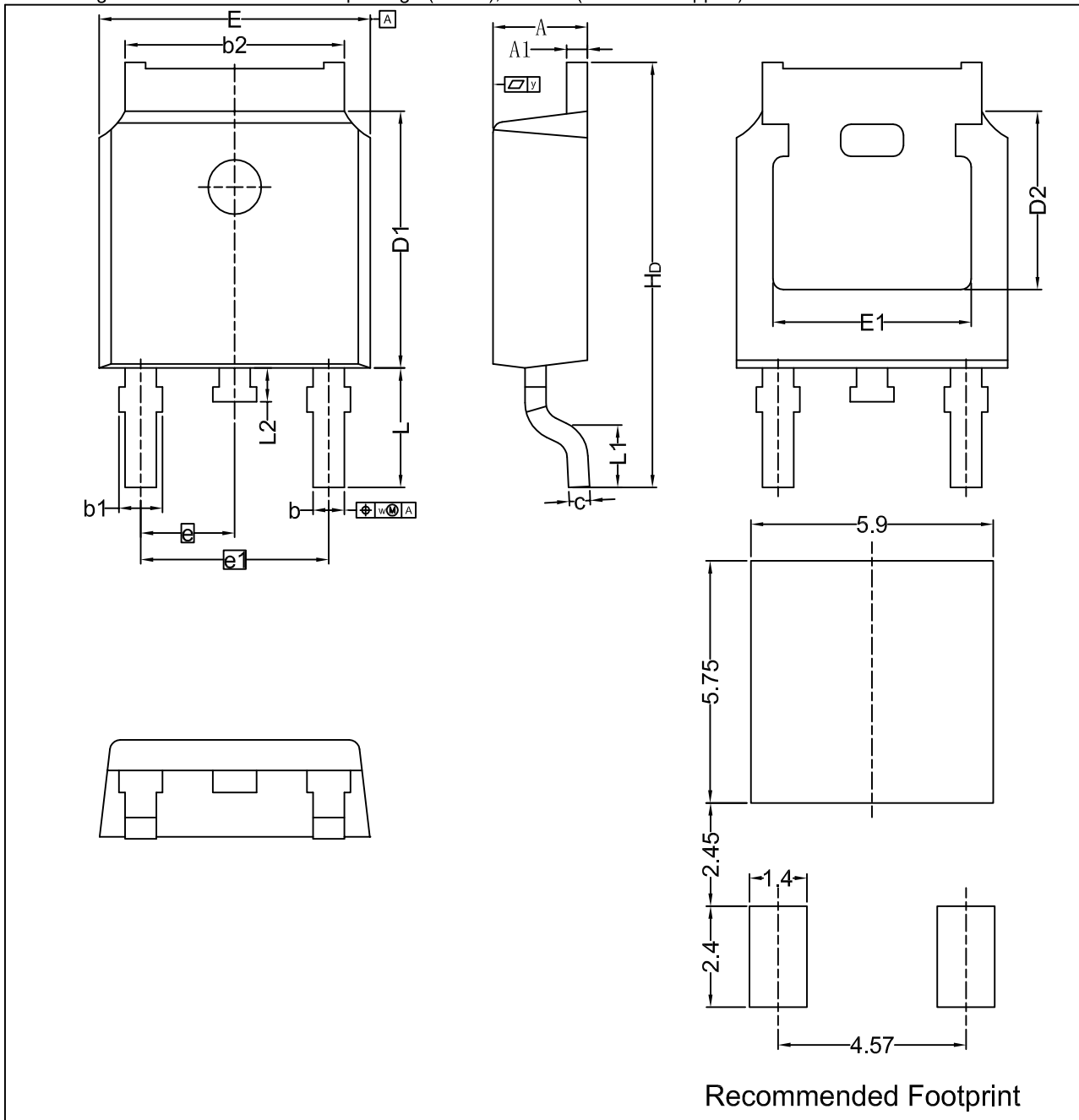
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MECHANICAL DATA

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H _D	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90	0.50	0.50	0.20	
mm nom														(Ref.)				
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40	---	0.90			0.20

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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